

WHAT IS CLAIMED IS:

1. A light emitting device, wherein:

a thin film transistor (TFT) is fabricated on an insulating base material;

a luminous section including a luminous material layer and
5 electrode layers supplying current to the luminous material layer are fabricated above the TFT; and

a predetermined pattern having a plurality of opening is developed to the insulating base material or at least one material placed
10 above the insulating base material and below the luminous material layer.

2. A light emitting device, wherein:

at least a first electrode layer to supply current to a luminous material layer, the luminous material layer emitting light by supplying current thereto, and a second electrode layer to supply current to the
5 luminous material layer are stacked above an insulating base material;

at least one of the first electrode layer and the second electrode layer is made of a transparent material; and

a predetermined pattern having a plurality of opening is developed to the electrode layer made of the transparent material, and
10 concavities and convexities are formed to the luminous material layer and the other electrode layer owing to the plurality of opening.

3. A light emitting device, wherein:

at least a first electrode layer to supply current to a luminous material layer, the luminous material layer emitting light by supplying current thereto, and a second electrode layer to supply current to the
5 luminous material layer are stacked above an insulating base material;

at least one of the first electrode layer and the second electrode

layer is made of a transparent material; and

the electrode layer made of the transparent material has a comb shape in plane view, and the luminous material layer and the other
 10 electrode layer stacked on the electrode layer made of the transparent material are formed in the shape of concavities and convexities in side view.

4. A light emitting device, wherein

a TFT is fabricated on an insulating base material;

at least an insulating layer, a first electrode layer to supply current to a luminous material layer, the luminous material layer
 5 emitting light by supplying current thereto, and a second electrode layer to supply current to the luminous material layer are stacked above the TFT;

the first electrode layer is made of a transparent material;

the second electrode layer is made of a reflecting material;

10 a predetermined pattern having a plurality of opening is formed to the insulating base material or at least one material placed above the insulating base material and below the luminous material layer; and

the first electrode layer is formed on convex sections of the
 15 insulating layer formed owing to the plurality of opening.

5. A light emitting device, wherein:

a TFT is fabricated on an insulating base material;

at least an insulating layer, a first electrode layer to supply current to a luminous material layer, the luminous material layer
 5 emitting light by supplying current thereto, and a second electrode layer to supply current to the luminous material layer are stacked above the TFT;

the second electrode layer is made of a transparent material;

the first electrode layer is made of a reflecting material;

10 a predetermined pattern having a plurality of opening is
formed to the insulating base material or at least one material placed
above the insulating base material and below the luminous material
layer; and

15 the second electrode layer is formed on concave sections of the
luminous material layer formed owing to the plurality of opening.

6. The light emitting device as claimed in claim 1, wherein
the luminous material layer is made of organic materials.

7. The light emitting device as claimed in claim 2, wherein
the luminous material layer is made of organic materials.

8. The light emitting device as claimed in claim 3, wherein
the luminous material layer is made of organic materials.

9. The light emitting device as claimed in claim 4, wherein
the luminous material layer is made of organic materials.

10. The light emitting device as claimed in claim 5, wherein
the luminous material layer is made of organic materials.

11. The light emitting device as claimed in claim 2, wherein:
the luminous material layer is made of inorganic materials;
a first insulating layer is formed between the luminous
material layer and the first electrode layer; and

5 a second insulating layer is formed between the luminous
material layer and the second electrode layer.

12. The light emitting device as claimed in claim 3, wherein:
 the luminous material layer is made of inorganic materials;
 a first insulating layer is formed between the luminous
 material layer and the first electrode layer; and

5 a second insulating layer is formed between the luminous
 material layer and the second electrode layer.

13. The light emitting device as claimed in claim 4, wherein:
 the luminous material layer is made of inorganic materials;
 a first insulating layer is formed between the luminous
 material layer and the first electrode layer; and

5 a second insulating layer is formed between the luminous
 material layer and the second electrode layer.

14. The light emitting device as claimed in claim 5, wherein:
 the luminous material layer is made of inorganic materials;
 a first insulating layer is formed between the luminous
 material layer and the first electrode layer; and

5 a second insulating layer is formed between the luminous
 material layer and the second electrode layer.

15. A production method of a light emitting device formed
 through a thin film transistor (TFT) fabrication process fabricating a TFT
 on an insulating base material and a luminous section fabrication process
 fabricating a luminous section including a luminous material layer and
 electrode layers supplying current to the luminous material layer above
 the TFT, comprising

a process of developing a predetermined pattern having a
 plurality of opening to the insulating base material or at least one

material placed above the insulating base material and below the
 10 luminous material layer in the TFT fabrication process or the luminous
 section fabrication process.

16. A production method of a light emitting device comprising
 steps of:

forming a first electrode layer to supply current to a luminous
 material layer above an insulating base material;

5 forming the luminous material layer emitting light by
 supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the
 luminous material layer on the luminous material layer, wherein:

at least one of the first electrode layer and the second electrode
 10 layer is made of a transparent material; and

a predetermined pattern having a plurality of opening is
 developed to the electrode layer made of the transparent material, and
 concavities and convexities are formed to the luminous material layer and
 the other electrode layer owing to the plurality of opening.

17. A production method of a light emitting device comprising
 steps of;

forming a first electrode layer to supply current to a luminous
 material layer above an insulating base material;

5 forming the luminous material layer emitting light by
 supplying current thereto on the first electrode layer; and

forming a second electrode layer to supply current to the
 luminous material layer on the luminous material layer, wherein:

at least one of the first electrode layer and the second electrode
 10 layer is made of a transparent material; and

the electrode layer made of the transparent material has a

comb shape in plane view, and the luminous material layer and the other electrode layer stacked on the electrode layer made of the transparent material are formed in the shape of concavities and convexities in side
 15 view.

18. A production method of a light emitting device comprising steps of:

fabricating a TFT on an insulating base material;

forming an insulating layer above the insulating base material
 5 on which the TFT is fabricated;

forming a first electrode layer to supply current to a luminous material layer on the insulating layer;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

10 forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

the first electrode layer is made of a transparent material;

the second electrode layer is made of a reflecting material;

a predetermined pattern having a plurality of opening is
 15 formed to the insulating base material or at least one material placed above the insulating base material and below the luminous material layer in the TFT fabrication process or the insulating layer forming process; and

the first electrode layer is formed on convex sections of the
 20 insulating layer formed owing to the plurality of opening.

19. A production method of a light emitting device comprising steps of:

fabricating a TFT on an insulating base material;

forming an insulating layer above the insulating base material

5 on which the TFT is fabricated;

forming a first electrode layer to supply current to a luminous material layer on the insulating layer;

forming the luminous material layer emitting light by supplying current thereto on the first electrode layer; and

10 forming a second electrode layer to supply current to the luminous material layer on the luminous material layer, wherein:

the second electrode layer is made of a transparent material;

the first electrode layer is made of a reflecting material;

15 a predetermined pattern having a plurality of opening is formed to the insulating base material or at least one material placed above the insulating base material and below the luminous material layer in the TFT fabrication process or the insulating layer forming process; and

20 the second electrode layer is formed on concave sections of the luminous material layer formed owing to the plurality of opening.